

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

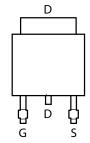
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

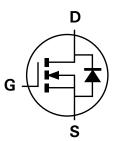
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.33 grams (approximate)







PIN OUT -TOP VIEW



Equivalent Circuit

Maximum Ratings @T_A = 25°C unless otherwise specified

Chara	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	10.0 6.5	А
Pulsed Drain Current (Note 4)			I _{DM}	48	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	1.71	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{0JA}	72.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

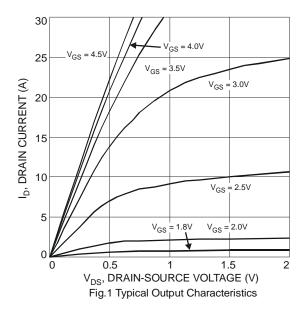


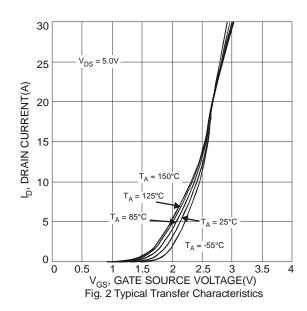
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	1	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	ı	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	1	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)	ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	8.0	-	1.6	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D		12 17	17	mΩ	$V_{GS} = 10V, I_D = 9A$	
Static Drain-Source On-Nesistance	R _{DS} (ON)	-	16	24		$V_{GS} = 4.5V, I_D = 7A$	
Forward Transfer Admittance	Y _{fs}	1	10	-	S	$V_{DS} = 10V, I_D = 9A$	
Diode Forward Voltage	V_{SD}	ı	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss	-	798	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	128	-	pF		
Reverse Transfer Capacitance	C_{rss}	ı	122	-	pF		
Gate Resistance	R_{g}	ı	1.37	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	ı	8.7	-	nC	V _{GS} = 5V, V _{DS} = 15V, I _D = 9A	
Gate-Source Charge	Q_{gs}	ı	1.7	-	nC		
Gate-Drain Charge	Q_{gd}	ı	2.4	-	nC		
Turn-On Delay Time	t _{D(on)}	ı	5.03	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_{L} = 15\Omega, R_{G} = 6\Omega, I_{D} = 1A$	
Turn-On Rise Time	t _r	ı	4.50	-	ns		
Turn-Off Delay Time	t _{D(off)}	ı	26.33	-	ns		
Turn-Off Fall Time	t _f	-	8.55	-	ns		

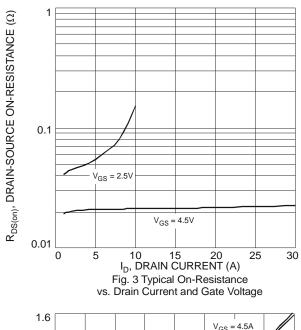
Notes:

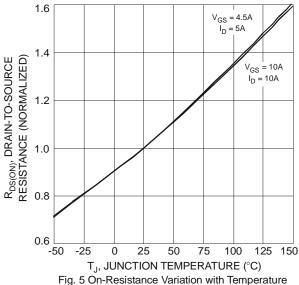
- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to production testing.

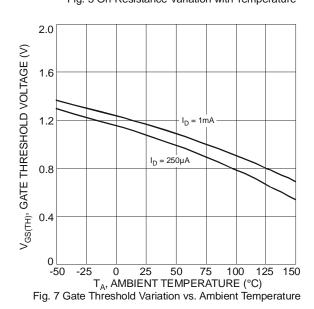


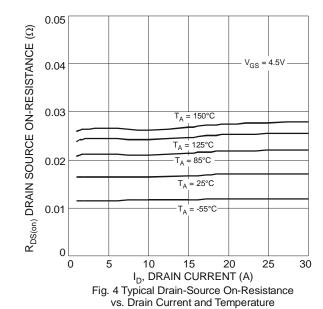












0.05 R_{DS(ON)} STATIC DRAIN SOURCE 0.04 ON-STATE RESISTANCE (\O) 0.03 $V_{GS} = 4.5A$ 0.02 0.01 V_{GS} = 10A I_D = 10A

-50

0 25 50 75 100 1 T_A AMBIENT TEMPERATURE (°C) Fig. 6 Typical Static Drain-Source On-State Resistance vs. Ambient Temperature

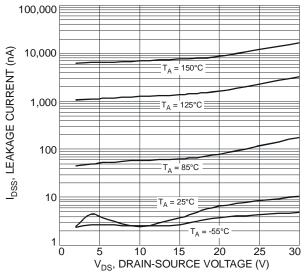
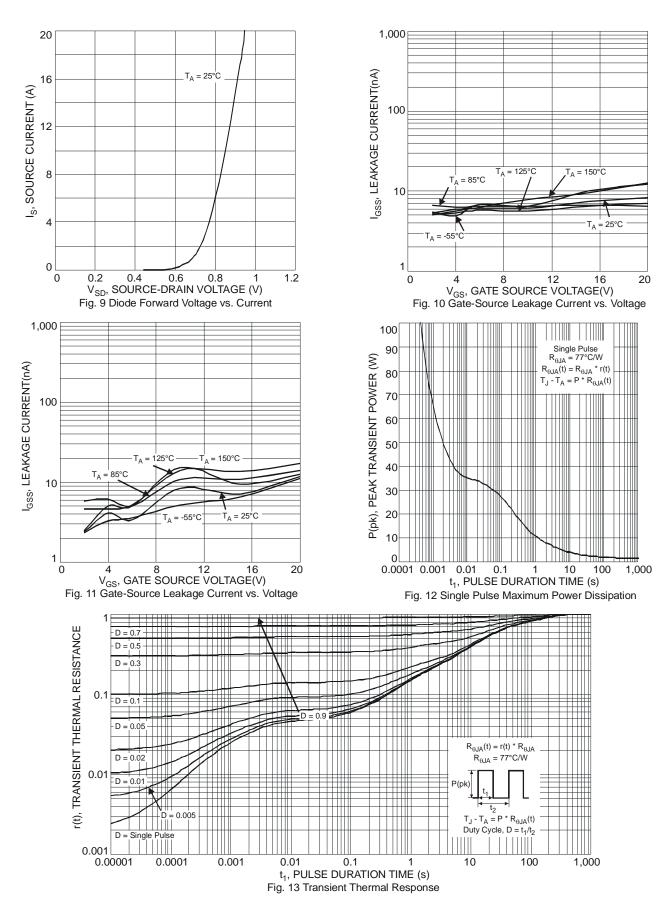


Fig. 8 Typical Drain-Source Leakage Current vs Voltage







Ordering Information (Note 7)

Part Number	Case	Packaging	
DMG4800LK3-13	TO252-3L	2500 / Tape & Reel	

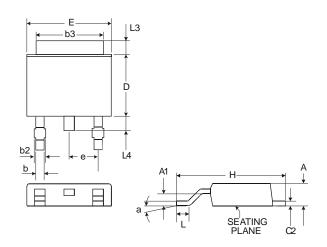
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



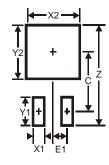
O!! = Manufacturer's Marking
N4800L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-52)

Package Outline Dimensions



TO252-3L					
Dim	Min	Тур	Max		
Α	2.19	2.29	2.39		
A1	0.97	1.07	1.17		
b	0.64	0.76	0.88		
b2	0.76	0.95	1.14		
b3	5.21	5.33	5.50		
C2	0.45	0.51	0.58		
D	6.00	6.10	6.20		
Е	6.45	6.58	6.70		
е	2.286 Typ.				
Н	9.40	9.91	10.41		
L	1.40	1.59	1.78		
L3	0.88	1.08	1.27		
L4	0.64	0.83	1.02		
а	0°	-	10°		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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